



- 1. G3 1.6um
- 2. 1200V 100A @ Tc= 100
- 3.
- 4.

Product Name	V <sub>CES</sub> (V)	I <sub>c</sub> (A)	V <sub>GE(th)</sub> (V)	V <sub>CE(sat)</sub> (V)	V <sub>F</sub> (V)	P <sub>d</sub> (W)	T <sub>j</sub>
DGQ100N120CTL2A	1200V	100A	5.8	1.5	2.00	883	-40~175

IGBT

To-247PLUS 1200V



# Originals

1. 600V breakdown voltage,  $I_{Tc} = 100A$
2. 600V breakdown voltage,  $I_{Tc} = 100A$
3. Low conduction loss, suitable for low to mid frequency applications
4. Strong short-circuit capacity

Yangjie Technology recently launched a new generation of  $600V$   $100A$   $SiC$  MOSFETs

New Product Announcement